

L Number	Hits	Search Text	DB	Time stamp
1	2102	((tab near3 lead) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:33
2	1640	((tab near3 lead) and semiconductor and (chip die wafer) ) and (lead with (electrode bump ball terminal pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:36
3	123	((((tab near3 lead) and semiconductor and (chip die wafer) ) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj hole)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:37
4	94	(((((tab near3 lead) and semiconductor and (chip die wafer) ) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj hole)))) and (seal sealed sealing encapsulant encapsulated encapsulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:38
5	43	(((((tab near3 lead) and semiconductor and (chip die wafer) ) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj hole)))) and (seal sealed sealing encapsulant encapsulated encapsulating)) and (stacked stacking)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:38